

10/773,228, Inter Ference, Class and Text SEARCH, REA
12-1-05.

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	233	((polymer or copolymer or resin or monomer) near3 sulfonate).clm.	US-PGPUB	OR	ON	2005/12/01 15:09
L2	90	(cyclohexyl adj acrylate or cyclohexylacrylate).clm.	US-PGPUB	OR	ON	2005/12/01 15:10
L3	84	(phenyl adj acrylate or phenylacrylate or hydroxyphenyl adj acrylate or hydroxyphenyl adj acrylate).clm.	US-PGPUB	OR	ON	2005/12/01 15:10
L4	0	(hydroxycyclohexyl adj acrylate or hydroxycyclohexylacrylate).clm.	US-PGPUB	OR	ON	2005/12/01 15:01
L5	0	(hydroxy\$1cyclohexyl adj acrylate or hydroxy\$1cyclohexylacrylate).clm.	US-PGPUB	OR	ON	2005/12/01 15:01
L6	0	1 and 2	US-PGPUB	OR	ON	2005/12/01 15:02
L7	0	1 and 3	US-PGPUB	OR	ON	2005/12/01 15:02
L8	442	(resist adj composition).clm.	US-PGPUB	OR	ON	2005/12/01 15:02
L9	7179	photoresist.clm.	US-PGPUB	OR	ON	2005/12/01 15:02
L10	1	1 and 8	US-PGPUB	OR	ON	2005/12/01 15:03
L11	1	1 and 9	US-PGPUB	OR	ON	2005/12/01 15:04
L12	1608	430/270.1.ccls. or 430/326.ccls.	US-PGPUB	OR	ON	2005/12/01 15:05
L13	107	526/243.ccls. or 526/287.ccls. or 528/391.ccls.	US-PGPUB	OR	ON	2005/12/01 15:05
L14	1873	526/243.ccls. or 526/287.ccls. or 528/391.ccls.	US-PGPUB; USPAT	OR	ON	2005/12/01 15:05
L15	5992	430/270.1.ccls. or 430/326.ccls.	US-PGPUB; USPAT	OR	ON	2005/12/01 15:05
L16	10	14 and 1	US-PGPUB; USPAT	OR	ON	2005/12/01 15:05
L17	3	15 and 1	US-PGPUB; USPAT	OR	ON	2005/12/01 15:08
L18	10181	(polymer or copolymer or resin or monomer) near3 sulfonate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:10
L19	5813	cyclohexyl adj acrylate or cyclohexylacrylate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:10

Text

↓

L20	5953	(phenyl adj acrylate or phenylacrylate or hydroxyphenyl adj acrylate or hydroxyphenyl adj acrylate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:11
L21	121	18 and 19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:23
L22	214	18 and 20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:11
L23	3871	styrene adj sulfonate or pyridinium adj sulfonate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:23
L24	92	21 not 23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:29
L25	154	22 not 23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:24
L26	3513	vinylsulfonate or vinyl adj sulfonate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:29
L27	12	25 and 26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:30

10/773,228 (12-28-04 = FD)
 STN REG file struc. search, Sulfonate monomers, 12/1/05
 claim 2, R&A

L9 ANSWER 1 OF 6 CAPLUS COPYRIGHT 2005 ACS on STN
 AN 2004:753223 CAPLUS
 DN 141:268557
 TI Positive resist composition and method of forming a resist pattern using the same
 IN Sasaki, Tomoya
 PA Fuji Photo Film Co., Ltd., Japan
 SO Eur. Pat. Appl., 80 pp.
 CODEN: EPXXDW
 DT Patent
 LA English
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	EP 1457819	A2	20040915	EP 2004-4961	20040303
	EP 1457819	A3	20050622		
	R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR, BG, CZ, EE, HU, PL, SK JP 2004279471	A2	20041007	JP 2003-67010	20030312
PRAI	JP 2003-67010	A	20030312		

AB A pos. photoresist composition comprises (A) a resin comprising specific repeating units and coming to have enhanced solubility in an alkaline developing solution by the action of an acid and (B) a compound generating an acid by the action of actinic rays or a radiation.

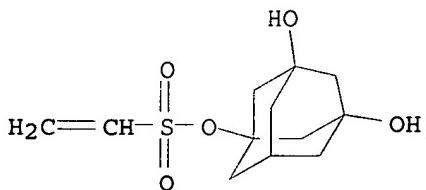
IT 756532-39-5P
 RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
 (pos. photoresist composition for forming resist pattern)

RN 756532-39-5 CAPLUS

CN Ethenesulfonic acid, 3,5-dihydroxytricyclo[3.3.1.13,7]dec-1-yl ester, polymer with 1-ethenyl-3,5-bis[1-(ethoxymethoxy)-2,2,2-trifluoro-1-(trifluoromethyl)ethyl]benzene (9CI) (CA INDEX NAME)

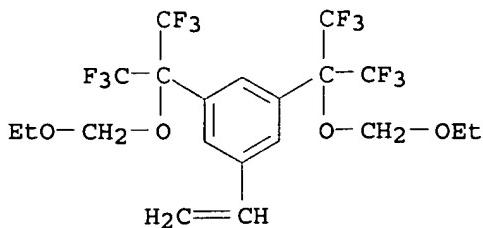
CM 1

CRN 677354-87-9
 CMF C12 H18 O5 S



CM 2

CRN 585573-40-6
 CMF C20 H20 F12 O4



L9 ANSWER 2 OF 6 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2004:291622 CAPLUS

DN 140:329533

TI Positive-working photoresist composition containing specific resin

IN Sasaki, Tomoya; Mizutani, Kazuyoshi; Kanna, Shinichi

PA Fuji Photo Film Co., Ltd., Japan

SO Jpn. Kokai Tokkyo Koho, 83 pp.

CODEN: JKXXXAF

DT Patent

LA Japanese

FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI JP 2004109834	A2	20040408	JP 2002-275241	20020920
PRAI JP 2002-275241		20020920		

AB The title composition contains a resin increasing the solubility in an alkali solution

by an acid and an actinic ray- or radiation sensitive acid-generator, wherein the resin has repeating unit [-C(R1)(R2)-C(R3)(-O-L1-[C(C(R21R22R23))(C(R24R25R26))]n-L2-C(OZa)(C(R27R28R29))(C(R30R31R32)))] (r1-3 = H, halo, cyano, alkyl; R21-32 = H, F, alkyl; L1-2 = single bond, 2-valent connecting group; n = 0, 1) and repeating unit containing the structure -[C(R4)(R5)]m-Z1-(X)p (R4-5 = alkyl; Z1 = (p+1)-valent alicyclic hydrocarbon; X = F, Cl, OH< etc.; m = 0, 1; p = integer 1-4). Composition is suitable for exposure beam of ≤160 nm and show good characteristics on development, image formation, dry etching resistance, etc.

IT 677354-89-1P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
(resin in pos.-working photoresist composition)

RN 677354-89-1 CAPLUS

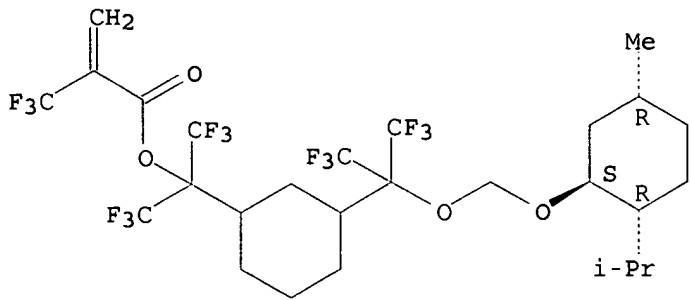
CN 2-Propenoic acid, 2-(trifluoromethyl)-, 2,2,2-trifluoro-1-(trifluoromethyl)-1-[3-[2,2,2-trifluoro-1-[(1S,2R,5R)-5-methyl-2-(1-methylethyl)cyclohexyl]oxy]methoxy]-1-(trifluoromethyl)ethyl)cyclohexyl]ethyl ester, polymer with 3,5-dihydroxytricyclo[3.3.1.13,7]dec-1-yl ethenesulfonate and 4-[[2-(ethenyl)ethoxy]methyl]-α,α'-bis(trifluoromethyl)tricyclo[3.3.1.13,7]decane-1-methanol (9CI) (CA INDEX NAME)

CM 1

CRN 677354-88-0

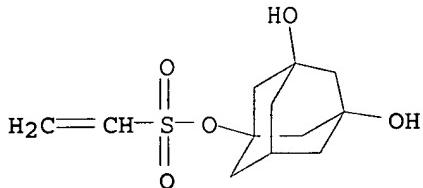
CMF C27 H33 F15 O4

Absolute stereochemistry.



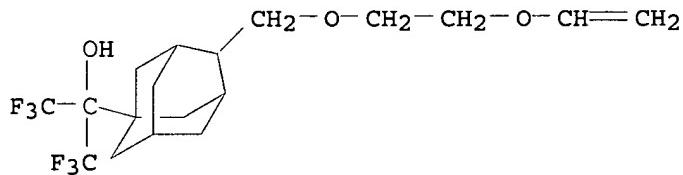
CM 2

CRN 677354-87-9
CMF C12 H18 O5 S



CM 3

CRN 677354-86-8
CMF C18 H24 F6 O3



L9 ANSWER 3 OF 6 CAPLUS COPYRIGHT 2005 ACS on STN
 AN 2003:658739 CAPLUS
 DN 140:33571
 TI A new photoresist materials for 157 nm lithography-3: Poly[2-hydroxy-3-pinanyl vinyl sulfonate-co-4-(1,1,1,3,3,3-hexafluoro-2-hydroxypropyl)styrene]
 AU Iimori, H.; Ando, S.; Shibasaki, Y.; Ueda, M.; Kishimura, S.; Endo, M.; Sasago, M.
 CS Department of Organic and Polymeric Materials, Tokyo Institute of Technology, Graduate School of Science and Engineering, Tokyo, 152-8552, Japan
 SO Journal of Photopolymer Science and Technology (2003), 16(4), 601-605
 CODEN: JSTEEW; ISSN: 0914-9244
 PB Technical Association of Photopolymers, Japan
 DT Journal
 LA English
 AB A new photoresist for 157 nm lithog. is based poly[(2-hydroxy-3-pinanyl vinyl sulfonate)-co-4-(1,1,1,3,3,3-hexafluoro-2-hydroxypropyl)styrene] [poly(VSO3Pina73-co-HFISt27)] and triphenylsulfonium perfluoro-1-

butanesulfonate (TPS-Nf) as a photoacid generator (PAG).
 Poly(VSO₃Pina-co-HF1St)s were prepared by free radical polymerization of VSO₃Pina with HF1St. The photoresist consisting of poly(VSO₃Pina73-co-HF1St27) and 4 wt% TPS-Nf showed a sensitivity of 10 mJ cm⁻² and a contrast of 6, when it was exposed to 157 nm laser and developed with 0.6 wt% aqueous tetramethylammonium hydroxide (TMAH) solution at 25 °C. A fine pos. image of 140 nm line and space patterns was printed in a film, which was exposed to 15 mJ cm⁻² by a contact printed mode. The resist film showed an optical d. (OD) value of 3.6 μm⁻¹ at 157 nm wavelength.

IT 479423-09-1P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
 (characterization of photoresist for vacuum-UV lithog. based on hydroxypinanylvinyl sulfonate-hexafluorohydroxypropylstyrene copolymer)

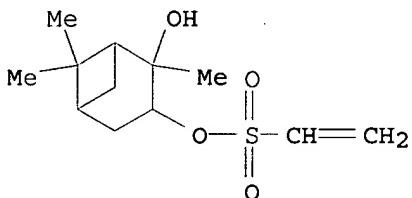
RN 479423-09-1 CAPLUS

CN Ethenesulfonic acid, 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ester, polymer with 4-ethenyl-α,α-bis(trifluoromethyl)benzenemethanol (9CI) (CA INDEX NAME)

CM 1

CRN 479423-01-3

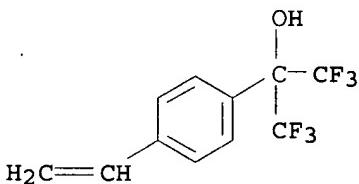
CMF C12 H20 O4 S



CM 2

CRN 2386-82-5

CMF C11 H8 F6 O

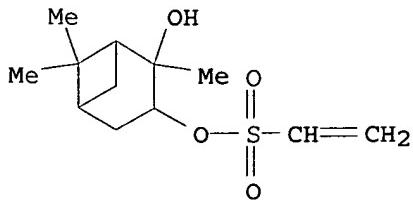


IT 479423-01-3P

RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT (Reactant or reagent)
 (copolyrn. with hexafluorohydroxypropylstyrene)

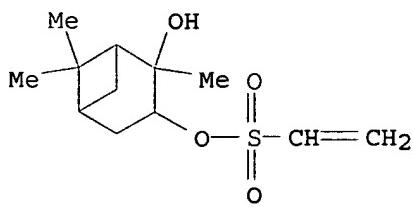
RN 479423-01-3 CAPLUS

CN Ethenesulfonic acid, 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ester (9CI) (CA INDEX NAME)



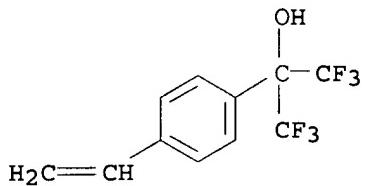
RE.CNT 20 THERE ARE 20 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

- L9 ANSWER 4 OF 6 CAPLUS COPYRIGHT 2005 ACS on STN
 AN 2003:242619 CAPLUS
 DN 138:278392
 TI Photoresist composition for pattern formation in making printed circuit boards
 IN Kishimura, Shinji; Endo, Masayuki; Sasago, Masaru; Ueda, Mitsuru; Fujigaya, Tsuyohiko
 PA Matsushita Electric Industrial Co., Ltd., Japan
 SO PCT Int. Appl., 59 pp.
 CODEN: PIXXD2
 DT Patent
 LA Japanese
 FAN.CNT 1
- | | PATENT NO. | KIND | DATE | APPLICATION NO. | DATE |
|------|--|------|----------|------------------|----------|
| PI | WO 2003025676 | A1 | 20030327 | WO 2002-JP9381 | 20020912 |
| | W: CN, JP, KR, US | | | | |
| | RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, SK, TR | | | | |
| | TW 589514 | B | 20040601 | TW 2002-91119405 | 20020827 |
| | EP 1403711 | A1 | 20040331 | EP 2002-765525 | 20020912 |
| | R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, FI, CY, TR, BG, CZ, EE, SK | | | | |
| | CN 1524200 | A | 20040825 | CN 2002-802641 | 20020912 |
| | US 2004029035 | A1 | 20040212 | US 2003-415272 | 20030428 |
| PRAI | JP 2001-277589 | A | 20010913 | | |
| | WO 2002-JP9381 | W | 20020912 | | |
| AB | Title photoresist composition comprises a base resin containing structural repeating unit $\text{CH}_2\text{CR}_1\text{SO}_3\text{R}_2$ and, other units such as $\text{CH}_2\text{CR}_3\text{C}_6\text{H}_4(\text{CH}_2)_m\text{C}(\text{CF}_3)_2\text{OR}_4$ and $\text{Q}(\text{CH}_2)_p\text{C}(\text{CF}_3)_2\text{OR}_6$ ($\text{C}_6\text{H}_4 = p\text{-phenylene}$; $\text{Q} = \text{norbornene residue}$; $\text{R}_1, \text{R}_3 = \text{H}, \text{Cl}, \text{F}, \text{alkyl}, \text{fluoroalkyl}$; $\text{R}_2, \text{R}_4, \text{R}_6 = \text{H}, \text{alkyl}, \text{alicyclic group}, \text{aromatic group}, \text{heterocycle}, \text{ester group}, \text{ether group}$; $m, p = 0\text{--}5$) and an acid generator. A pattern-forming method is characterized by exposure to light having wave length <180 nm. | | | | |
| IT | 479423-09-1D, reaction products 503178-58-3
503178-59-4D, reaction products 503178-60-7
503178-64-1 | | | | |
| | RL: POF (Polymer in formulation); TEM (Technical or engineered material use); USES (Uses)
(photoresist composition for pattern formation in making printed circuit boards) | | | | |
| RN | 479423-09-1 CAPLUS | | | | |
| CN | Ethenesulfonic acid, 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ester, polymer with 4-ethenyl- α,α' -bis(trifluoromethyl)benzenemethanol (9CI) (CA INDEX NAME) | | | | |
| CM | 1 | | | | |
| CRN | 479423-01-3 | | | | |
| CMF | C12 H20 O4 S | | | | |



CM 2

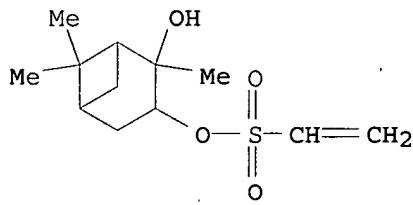
CRN 2386-82-5
CMF C11 H8 F6 O



RN 503178-58-3 CAPLUS
CN Ethenesulfonic acid, 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ester, homopolymer (9CI) (CA INDEX NAME)

CM 1

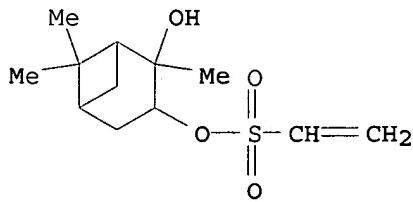
CRN 479423-01-3
CMF C12 H20 O4 S



RN 503178-59-4 CAPLUS
CN Ethenesulfonic acid, polymer with 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ethenesulfonate (9CI) (CA INDEX NAME)

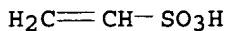
CM 1

CRN 479423-01-3
CMF C12 H20 O4 S



CM 2

CRN 1184-84-5
CMF C2 H4 O3 S

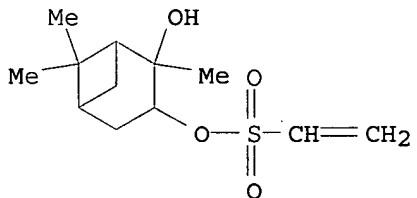


RN 503178-60-7 CAPLUS

CN Carbonic acid, 1,1-dimethylethyl 1-(4-ethenylphenyl)-2,2,2-trifluoro-1-(trifluoromethyl)ethyl ester, polymer with 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ethenesulfonate (9CI) (CA INDEX NAME)

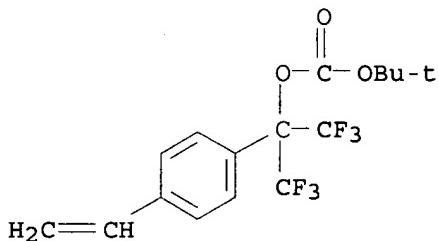
CM 1

CRN 479423-01-3
CMF C12 H20 O4 S



CM 2

CRN 143336-93-0
CMF C16 H16 F6 O3

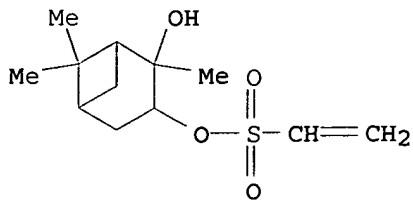


RN 503178-64-1 CAPLUS

CN Carbonic acid, 1,1-dimethylethyl 1-(4-ethenylphenyl)-2,2,2-trifluoro-1-(trifluoromethyl)ethyl ester, polymer with 4-ethenyl- α,α -bis(trifluoromethyl)benzenemethanol and 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ethenesulfonate (9CI) (CA INDEX NAME)

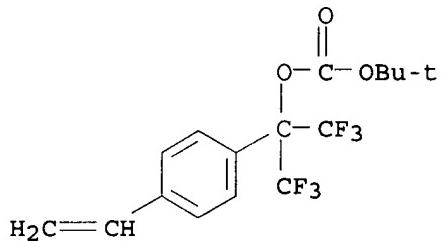
CM 1

CRN 479423-01-3
CMF C12 H20 O4 S



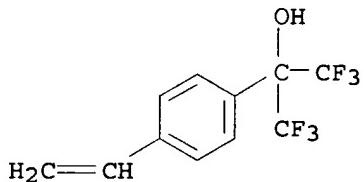
CM 2

CRN 143336-93-0
CMF C16 H16 F6 O3



CM 3

CRN 2386-82-5
CMF C11 H8 F6 O



RE.CNT 13 THERE ARE 13 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

- L9 ANSWER 5 OF 6 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2002:633341 CAPLUS
DN 138:63741
TI A new photoresist material for 157 nm lithography-2
AU Fujigaya, T.; Ando, S.; Shibasaki, Y.; Kishimura, S.; Endo, M.; Sasago, M.; Ueda, M.
CS Department of Organic and Polymeric Materials, Tokyo Institute of Technology, Tokyo, 152-8552, Japan
SO Journal of Photopolymer Science and Technology (2002), 15(4), 643-654
CODEN: JSTEEW; ISSN: 0914-9244
PB Technical Association of Photopolymers, Japan
DT Journal
LA English
AB Time-dependent d. functional theory (TD-DFT) calcns. using the B3LYP hybrid functional suggested that sulfonic acid esters are transparent at around 157 nm region. Based on these findings, poly(vinyl methylsulfonate) [poly(VSO₃Me)] was prepared and found to have an extremely low absorbance (Absolute) of 2.2 μm⁻¹ at 157 nm. Various vinyl

alkylsulfonates (VSO_3R)s were prepared from 2-chloroethanesulfonyl chloride and alc. components in the presence of pyridine, and their radical polymns. were conducted in bulk using 2,2'-azobis(isobutyronitrile) as an initiator. Polymns. of primary and secondary VSO_3Rs bearing small alkyl substituents gave homopolymers with high mol. wts. Among them, the Absolute of poly(vinyl 2,2,2-trifluoroethylsulfonate) reached $1.3 \mu\text{m}^{-1}$. Various copolymers from vinyl alkylsulfonates and 4-(1,1,1,3,3,3-hexafluoro-2-hydroxypropyl)styrene (HFIST) were also prepared and the Absolute of poly(vinyl 1,1,1,3,3,3-hexafluoroisopropylsulfonate40-co-HFIST60) [poly($\text{VSO}_3\text{iPr}_6\text{F40}$ -co-HFIST60)] was found to be $2.4 \mu\text{m}^{-1}$ at 157 nm. The photoresist consisting of partially tert-butoxycarbonyl-protected poly($\text{VSO}_3\text{iPr}_6\text{F40}$ -co-HFIST28-co-t-BOCHFIST32) (Absolute 2.6) and an photoacid generator showed the contrast and sensitivity of 10.3 and 5.0 mJ cm^{-2} , resp. Attention: 2-chloroethanesulfonyl chloride, vinyl 2,2,2-trifluoroethylsulfonate and vinyl 1,1,1,3,3,3-hexafluoroisopropylsulfonate are severe eye and skin irritants.

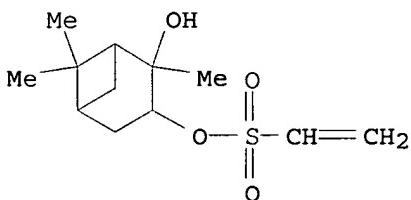
IT 479423-01-3P

RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT (Reactant or reagent)

(copolymer with hexafluorohydroxypropylstyrene in preparation of polymers for vacuum-UV photoresist applications)

RN 479423-01-3 CAPLUS

CN Ethenesulfonic acid, 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ester (9CI) (CA INDEX NAME)



IT 479423-09-1P

RL: PRP (Properties); SPN (Synthetic preparation); PREP (Preparation) (thermal properties and calcn. of vacuum-UV spectra of vinyl alkylsulfonate-(hexafluorohydroxypropyl)styrene copolymers for photoresist applications)

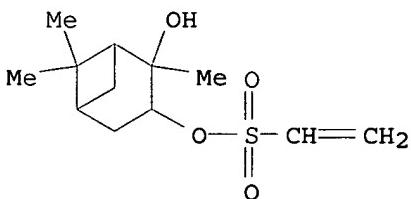
RN 479423-09-1 CAPLUS

CN Ethenesulfonic acid, 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ester, polymer with 4-ethenyl- α,α -bis(trifluoromethyl)benzenemethanol (9CI) (CA INDEX NAME)

CM 1

CRN 479423-01-3

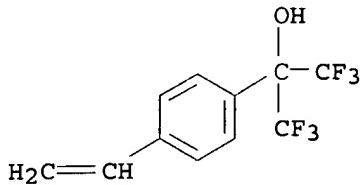
CMF C12 H20 O4 S



CM 2

CRN 2386-82-5

CMF C11 H8 F6 O



RE.CNT 38 THERE ARE 38 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L9 ANSWER 6 OF 6 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2000:585594 CAPLUS

DN 133:200844

TI Positive-working photoresist composition containing polymer having sulfonate group

IN Sato, Kenichiro; Kodama, Kunihiko; Aogo, Toshiaki

PA Fuji Photo Film Co., Ltd., Japan

SO Jpn. Kokai Tokkyo Koho, 47 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 2

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2000231194	A2	20000822	JP 1999-240600	19990826
	KR 2000047927	A	20000725	KR 1999-55067	19991206
	US 6576392	B1	20030610	US 1999-456827	19991206
PRAI	JP 1998-347193	A	19981207		
	JP 1999-30209	A	19990208		
	JP 1999-240600	A	19990826		

AB The title photoresist composition contains a compound which generates an acid by

irradiation with activating ray or radiation and a resin which contains a repeating unit having SO₂OR group [R = alkyl, cycloalkyl, alkenyl (these groups may be substituted)] and of which the dissoln. rate to alkaline developing solns. increases by the action of acid. The composition shows high sensitivity toward far UV rays, especially KrF or ArF excimer laser beams and good developability and provides high resolution patterns with improved coarse-dense dependence.

IT 289040-37-5D, hydrolyzed

RL: TEM (Technical or engineered material use); USES (Uses)
(photoresist composition containing alkali-soluble polymer with sulfonate group)

RN 289040-37-5 CAPLUS

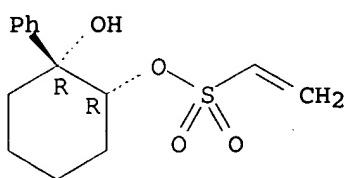
CN Ethenesulfonic acid, (1R,2R)-2-hydroxy-2-phenylcyclohexyl ester, rel-, polymer with 1-[1-(1,1-dimethylethoxy)ethoxy]-4-ethenylbenzene and 4-ethenylphenol (9CI) (CA INDEX NAME)

CM 1

CRN 289040-36-4

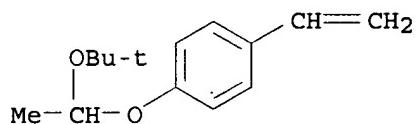
CMF C14 H18 O4 S

Relative stereochemistry.



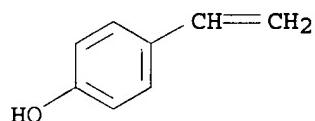
CM 2

CRN 169811-45-4
CMF C14 H20 O2



CM 3

CRN 2628-17-3
CMF C8 H8 O



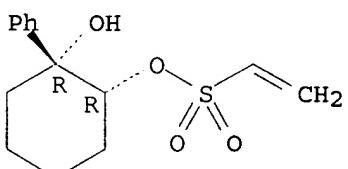
IT 289040-36-4P

RL: PNU (Preparation, unclassified); RCT (Reactant); PREP (Preparation);
RACT (Reactant or reagent)
(preparation and polymerization of)

RN 289040-36-4 CAPLUS

CN Ethenesulfonic acid, (1R,2R)-2-hydroxy-2-phenylcyclohexyl ester, rel-
(9CI) (CA INDEX NAME)

Relative stereochemistry.



=>

L10 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2005 ACS on STN
AN 1993:682319 CAPLUS
DN 119:282319
TI Ink ribbon and printing paper for thermal recording
IN Shinozaki, Kenji
PA Sony Corp., Japan
SO Jpn. Kokai Tokkyo Koho, 12 pp.
CODEN: JKXXAF
DT Patent
LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 05112080	A2	19930507	JP 1991-303977	19911023
PRAI	JP 1991-303977		19911023		

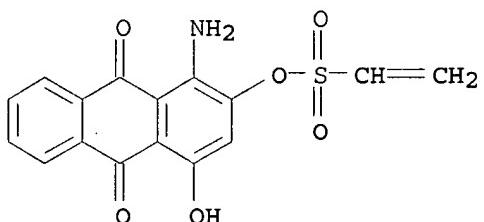
AB The method involves transferring a dye containing I (X = Cl, F; Y = Cl, OMe, NHR, SO₂, CH:CH₂; R = alkyl), II (X₁, Y₁ = Cl, F, SO₂, Me; Z = Cl, Me, F), and/or III (X₂, Y₂ = Cl, F) to a receiving layer with an OH- or NH₂-containing resin by applying a thermal energy and fixing. The ribbon contains a substrate coated with an ink layer containing the dye. The paper contains a receiving layer, fixed by the dye, containing the resin and an electrolyte on a substrate.

IT 151453-30-4

RL: DEV (Device component use); USES (Uses)
(ink ribbon containing, for thermal-transfer recording)

RN 151453-30-4 CAPLUS

CN Ethenesulfonic acid, 1-amino-9,10-dihydro-4-hydroxy-9,10-dioxo-2-anthracenyl ester (9CI) (CA INDEX NAME)



=>

=> d bib ab hitstr

L20 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2004:963502 CAPLUS

DN 141:417925

TI Positive-working vacuum-UV photoresist composition and patterning method
using the same

IN Sasaki, Tomoya

PA Fuji Photo Film Co., Ltd., Japan

SO Jpn. Kokai Tokkyo Koho, 99 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI JP 2004318046	A2	20041111	JP 2003-293188	20030813
PRAI JP 2003-94329	A	20030331		

AB Disclosed is the pos.-working vacuum-UV photoresist composition especially suited for

a F2 excimer laser (157 nm) comprising (a) a resin having a repeating unit FR0C-CFR1, FR0C-CF(OR2), and/or F(R3O)C-CFR4 (R0,1 = H, F, alkyl, cycloalkyl, etc.; R2-4 = alkyl, cycloalkyl, etc.), and (b) a photoacid.

IT 791849-10-0

RL: PRP (Properties); TEM (Technical or engineered material use); USES (Uses)

(pos.-working vacuum-UV photoresist composition containing fluoropolymer and photoacid)

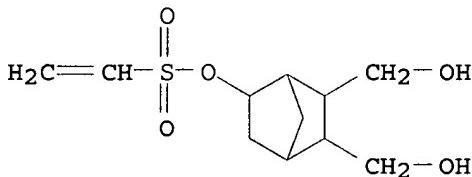
RN 791849-10-0 CAPLUS

CN Ethenesulfonic acid, 5,6-bis(hydroxymethyl)bicyclo[2.2.1]hept-2-yl ester, polymer with 5-[2-(ethoxymethoxy)-3,3,3-trifluoro-2-(trifluoromethyl)propyl]bicyclo[2.2.1]hept-2-ene and 1,1,2,3,3,3-hexafluoro-1-propene (9CI) (CA INDEX NAME)

CM 1

CRN 791849-09-7

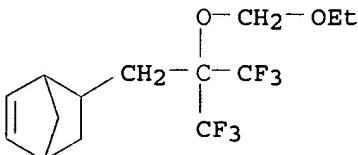
CMF C11 H18 O5 S



CM 2

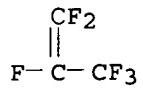
CRN 328114-61-0

CMF C14 H18 F6 O2

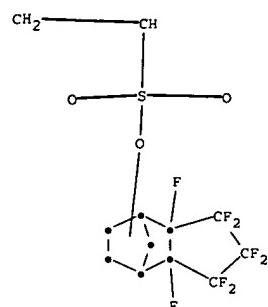


CM 3

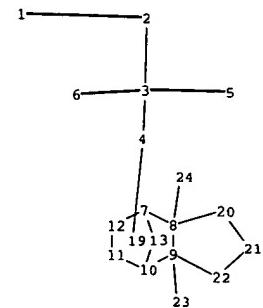
CRN 116-15-4
CMF C3 F6



=>

Ak_g¹1_{E_g}¹

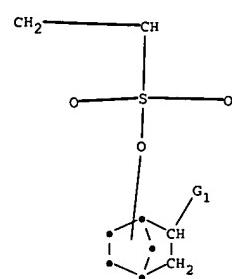
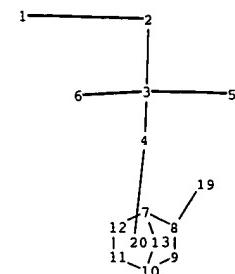
17



chain nodes :
 1 2 3 4 5 6 15 17 23 24
 ring nodes :
 7 8 9 10 11 12 13 20 21 22
 chain bonds :
 1-2 2-3 3-4 3-5 3-6 8-24 9-23 15-17
 ring bonds :
 7-8 7-12 7-13 8-9 8-20 9-10 9-22 10-11 10-13 11-12 20-21 21-22
 exact/norm bonds :
 2-3 3-4 3-5 3-6 7-8 7-12 7-13 8-9 8-20 9-10 9-22 10-11 10-13
 11-12 15-17 20-21 21-22
 exact bonds :
 1-2 8-24 9-23

G1:CF2,CF3,[*1]

Match level :
 1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom
 10:Atom 11:Atom 12:Atom 13:Atom 15:CLASS 17:CLASS 19:CLASS 20:CLASS
 21:Atom 22:Atom 23:CLASS 24:CLASS
 Element Count :
 Node 15: Limited
 C,C1-20

Ak₀¹15₀¹
17

chain nodes :
 1 2 3 4 5 6 15 17 19
 ring nodes :
 7 8 9 10 11 12 13
 chain bonds :
 1-2 2-3 3-4 3-5 3-6 8-19 15-17
 ring bonds :
 7-8 7-12 7-13 8-9 9-10 10-11 10-13 11-12
 exact/norm bonds :
 2-3 3-4 3-5 3-6 7-8 7-12 7-13 8-9 8-19 9-10 10-11 10-13 11-12
 15-17
 exact bonds :
 1-2

G1:CF2,CF3,[*1]

Match level :
 1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom
 10:Atom 11:Atom 12:Atom 13:Atom 15:CLASS 17:CLASS 19:CLASS 20:CLASS
 Element Count :
 Node 15: Limited
 C,C1-20

(FILE 'HOME' ENTERED AT 13:11:30 ON 01 DEC 2005)

FILE 'REGISTRY' ENTERED AT 13:11:35 ON 01 DEC 2005

L1 STRUCTURE UPLOADED
L2 STRUCTURE UPLOADED
L3 STRUCTURE UPLOADED
L4 STRUCTURE UPLOADED
L5 0 S L1 FULL
L6 0 S L2 FULL
L7 11 S L3 FULL
L8 2 S L4 FULL

FILE 'CAPLUS' ENTERED AT 13:16:14 ON 01 DEC 2005

L9 6 S L7
L10 1 S L8

FILE 'REGISTRY' ENTERED AT 13:19:01 ON 01 DEC 2005

L11 STRUCTURE UPLOADED
L12 STRUCTURE UPLOADED
L13 STRUCTURE UPLOADED
L14 STRUCTURE UPLOADED
L15 STRUCTURE UPLOADED
L16 0 S L11 FULL
L17 0 S L12 FULL
L18 0 S L13 FULL
L19 2 S L14 FULL

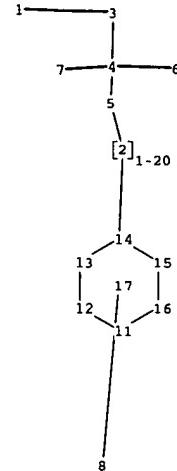
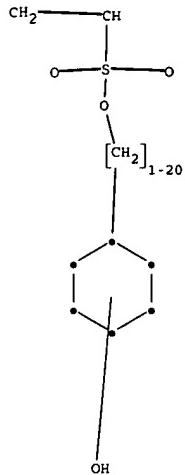
FILE 'CAPLUS' ENTERED AT 13:22:01 ON 01 DEC 2005

L20 1 S L19

FILE 'REGISTRY' ENTERED AT 13:32:50 ON 01 DEC 2005

L21 STRUCTURE UPLOADED
L22 STRUCTURE UPLOADED
L23 0 S L21 FULL
L24 0 S L22 FULL

=>



chain nodes :
1 2 3 4 5 6 7 8

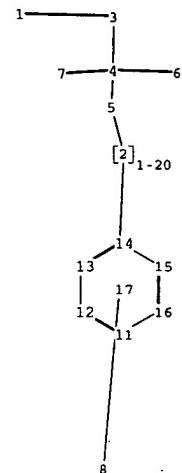
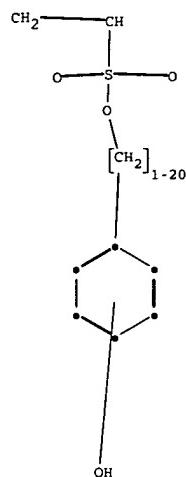
ring nodes :
11 12 13 14 15 16

chain bonds :
1-3 2-5 2-14 3-4 4-5 4-6 4-7

ring bonds :
11-12 11-16 12-13 13-14 14-15 15-16

exact bonds :
1-3 2-5 2-14 3-4 4-5 4-6 4-7 11-12 11-16 12-13 13-14 14-15
15-16

Match level :
1:CLASS 2:CLASS 3:CLASS 4:CLASS 5:CLASS 6:CLASS 7:CLASS 8:CLASS
11:Atom 12:Atom 13:Atom 14:Atom 15:Atom 16:Atom 17:CLASS

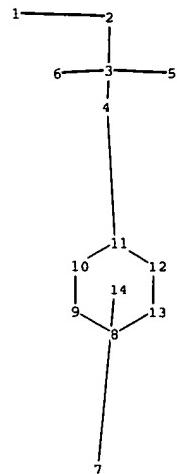
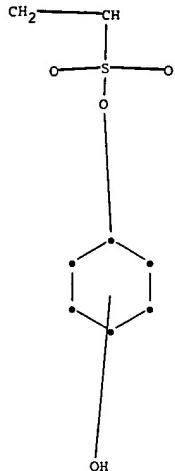


```

chain nodes :
 1 2 3 4 5 6 7 8
ring nodes :
 11 12 13 14 15 16
chain bonds :
 1-3 2-5 2-14 3-4 4-5 4-6 4-7
ring bonds :
 11-12 11-16 12-13 13-14 14-15 15-16
exact bonds :
 1-3 2-5 2-14 3-4 4-5 4-6 4-7
normalized bonds :
 11-12 11-16 12-13 13-14 14-15 15-16

Match level :
 1:CLASS 2:CLASS 3:CLASS 4:CLASS 5:CLASS 6:CLASS 7:CLASS 8:CLASS
 11:Atom 12:Atom 13:Atom 14:Atom 15:Atom 16:Atom 17:CLASS

```

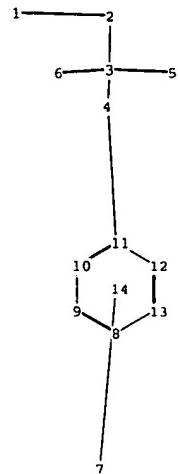
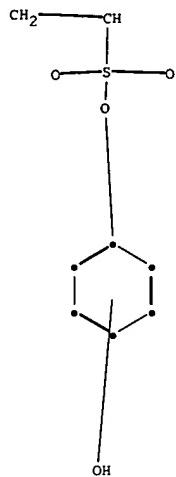


```

chain nodes :
 1 2 3 4 5 6 7
ring nodes :
 8 9 10 11 12 13
chain bonds :
 1-2 2-3 3-4 3-5 3-6 4-11
ring bonds :
 8-9 8-13 9-10 10-11 11-12 12-13
exact/norm bonds :
 4-11
exact bonds :
 1-2 2-3 3-4 3-5 3-6 8-9 8-13 9-10 10-11 11-12 12-13

Match level :
 1:CLASS 2:CLASS 3:CLASS 4:CLASS 5:CLASS 6:CLASS 7:CLASS 8:Atom
 9:Atom 10:Atom 11:Atom 12:Atom 13:Atom 14:CLASS

```

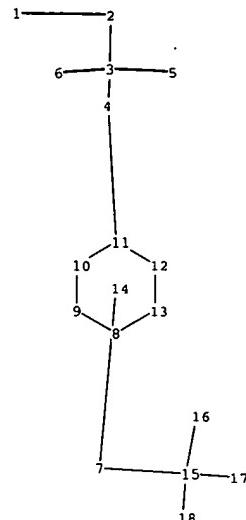
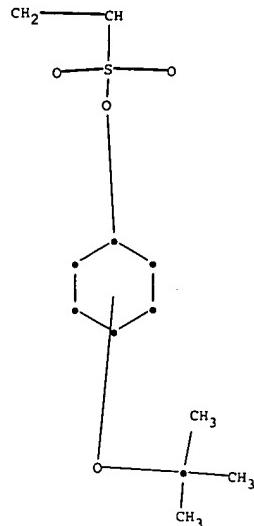


```

chain nodes :
 1 2 3 4 5 6 7
ring nodes :
 8 9 10 11 12 13
chain bonds :
 1-2 2-3 3-4 3-5 3-6 4-11
ring bonds :
 8-9 8-13 9-10 10-11 11-12 12-13
exact/norm bonds :
 4-11
exact bonds :
 1-2 2-3 3-4 3-5 3-6
normalized bonds :
 8-9 8-13 9-10 10-11 11-12 12-13

Match level :
 1:CLASS 2:CLASS 3:CLASS 4:CLASS 5:CLASS 6:CLASS 7:CLASS 8:Atom
 9:Atom 10:Atom 11:Atom 12:Atom 13:Atom 14:CLASS

```

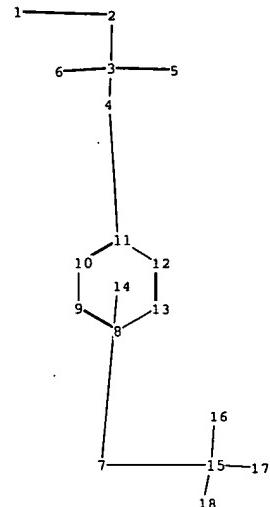
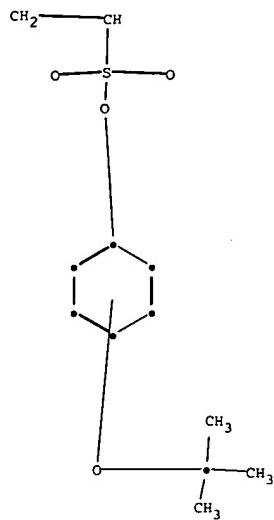


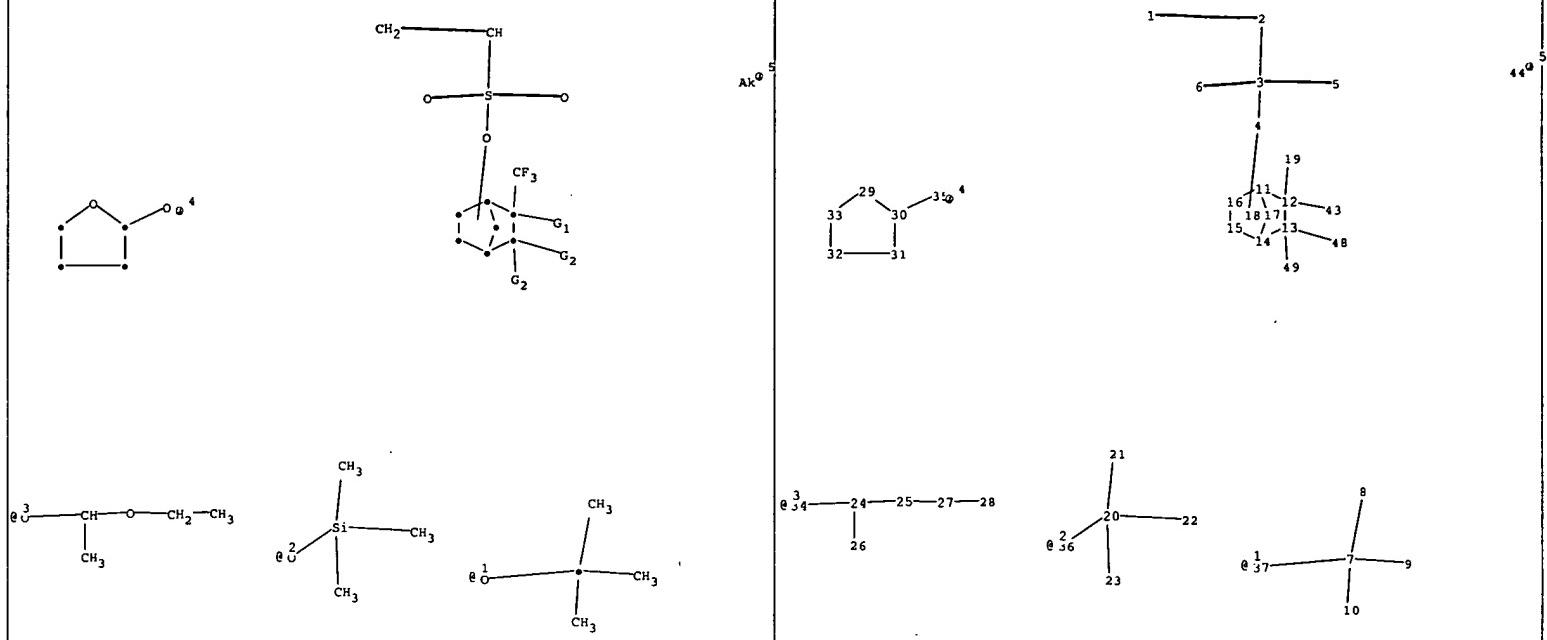
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chain nodes :
 1 2 3 4 5 6 7 15 16 17 18
ring nodes :
 8 9 10 11 12 13
chain bonds :
 1-2 2-3 3-4 3-5 3-6 4-11 7-15 15-16 15-17 15-18
ring bonds :
 8-9 8-13 9-10 10-11 11-12 12-13
exact/norm bonds :
 7-15
exact bonds :
 1-2 2-3 3-4 3-5 3-6 4-11 8-9 8-13 9-10 10-11 11-12 12-13 15-16
 15-17 15-18

Match level :
 1:CLASS 2:CLASS 3:CLASS 4:CLASS 5:CLASS 6:CLASS 7:CLASS 8:Atom
 9:Atom 10:Atom 11:Atom 12:Atom 13:Atom 14:CLASS 15:CLASS 16:CLASS
 17:CLASS 18:CLASS

```





chain nodes :
 1 2 3 4 5 6 7 8 9 10 19 20 21 22 23 24 25 26 27 28 34
 35 36 37 43 44 48 49
 ring nodes :
 11 12 13 14 15 16 17 29 30 31 32 33
 chain bonds :
 1-2 2-3 3-4 3-5 3-6 7-10 7-8 7-9 7-37 12-19 12-43 13-48 13-49
 20-21 20-22 20-23 20-36 24-25 24-26 24-34 25-27 27-28 30-35
 ring bonds :
 11-12 11-16 11-17 12-13 13-14 14-15 14-17 15-16 29-30 29-33 30-31
 31-32 32-33
 exact/norm bonds :
 2-3 3-4 3-5 3-6 7-37 11-12 11-16 11-17 12-13 12-43 13-14 13-48
 13-49 14-15 14-17 15-16 24-25 24-34 29-30 29-33 30-31 30-35 31-32
 32-33
 exact bonds :
 1-2 7-10 7-8 7-9 12-19 20-21 20-22 20-23 20-36 24-26 25-27 27-28

G1:OH, [*1], [*2], [*3], [*4]

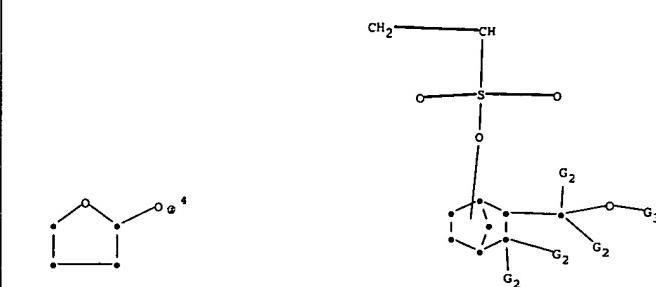
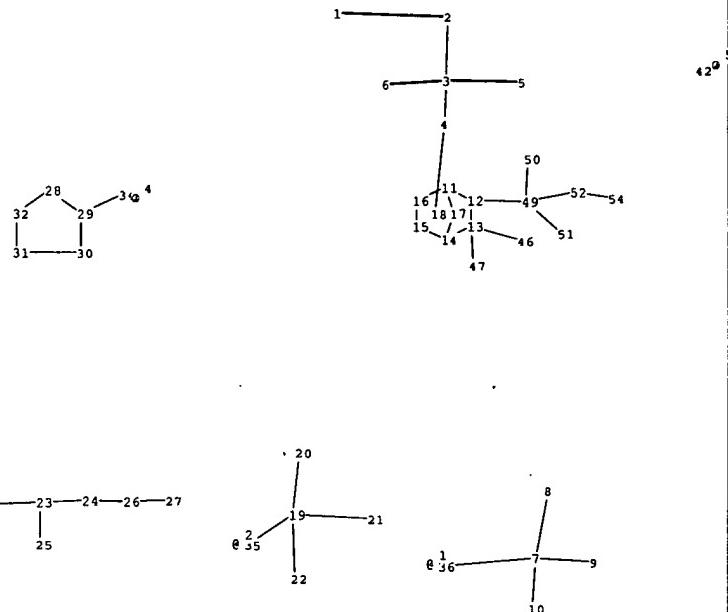
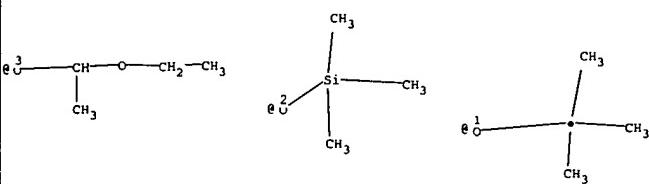
G2:H,F,CF2,CF3, [*5]

Match level :

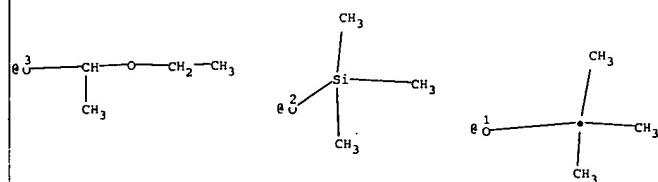
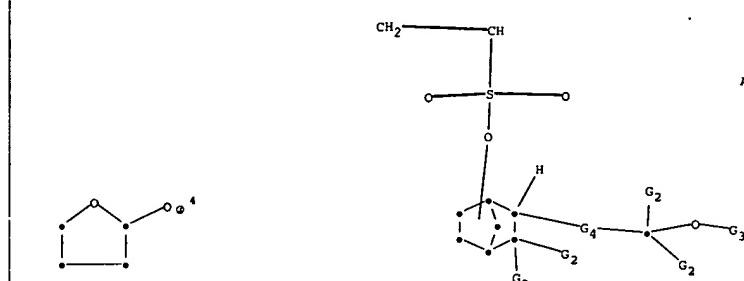
1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom
 10:Atom 11:Atom 12:Atom 13:Atom 14:Atom 15:Atom 16:Atom 17:Atom
 18:Atom 19:Atom 20:CLASS 21:Atom 22:Atom 23:Atom 24:Atom 25:Atom
 26:Atom 27:Atom 28:Atom 29:Atom 30:Atom 31:Atom 32:Atom 33:Atom
 34:Atom 35:Atom 36:Atom 37:Atom 43:Atom 44:Atom 48:CLASS 49:CLASS

Element Count :

Node 44: Limited
 C,Cl-20

Ak²

Node 42: Limited
C,C1-20

Ak⁹Ak³Ak⁵Ak²Ak¹Ak⁴Ak⁶Ak⁷Ak⁸Ak⁰Ak⁵Ak²Ak¹Ak⁴Ak⁶Ak⁷Ak⁸Ak⁹Ak⁰Ak⁵Ak²Ak¹Ak⁴

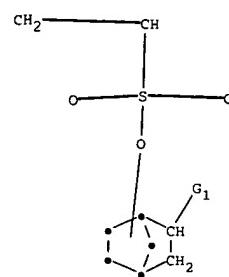
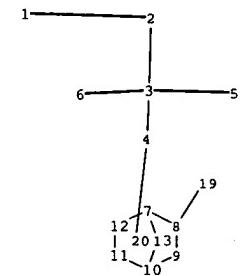
Ak<sup

52:CLASS 54:CLASS 56:CLASS 57:CLASS

Element Count :

Node 42: Limited

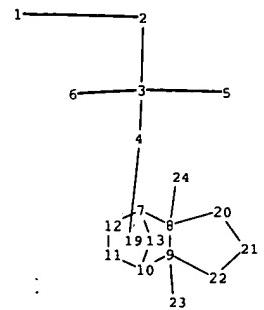
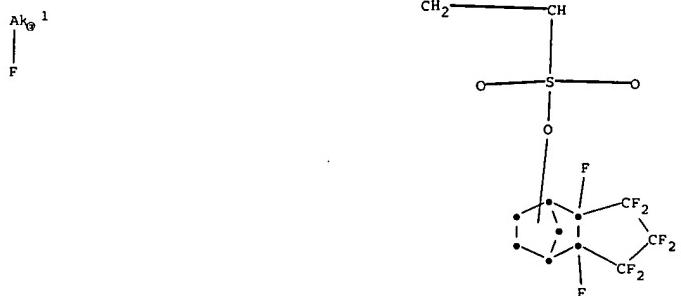
C,C1-20

Ak₀¹15₀¹
17

chain nodes :
 1 2 3 4 5 6 15 17 19
 ring nodes :
 7 8 9 10 11 12 13
 chain bonds :
 1-2 2-3 3-4 3-5 3-6 8-19 15-17
 ring bonds :
 7-8 7-12 7-13 8-9 9-10 10-11 10-13 11-12
 exact/norm bonds :
 2-3 3-4 3-5 3-6 7-8 7-12 7-13 8-9 8-19 9-10 10-11 10-13 11-12
 15-17
 exact bonds :
 1-2

G1:CF2,CF3,[*1]

Match level :
 1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom
 10:Atom 11:Atom 12:Atom 13:Atom 15:CLASS 17:CLASS 19:CLASS 20:CLASS
 Element Count :
 Node 15: Limited
 C,C1-20



```

chain nodes :
  1  2  3  4  5  6  15  17  23  24
ring nodes :
  7  8  9  10 11 12 13 20 21 22
chain bonds :
  1-2  2-3  3-4  3-5  3-6  8-24  9-23  15-17
ring bonds :
  7-8  7-12  7-13  8-9  8-20  9-10  9-22  10-11  10-13  11-12  20-21  21-22
exact/norm bonds :
  2-3  3-4  3-5  3-6  7-8  7-12  7-13  8-9  8-20  9-10  9-22  10-11  10-13
  11-12  15-17  20-21  21-22
exact bonds :
  1-2  8-24  9-23

```

G1:CF2, CF3, [*1]

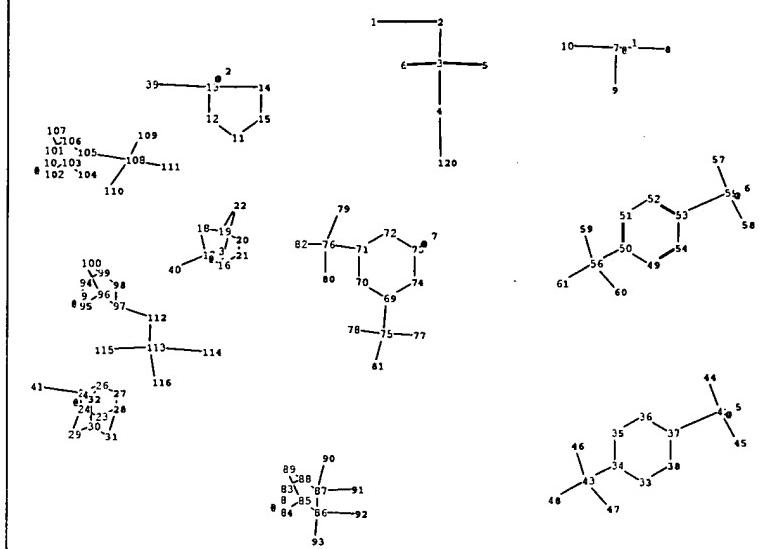
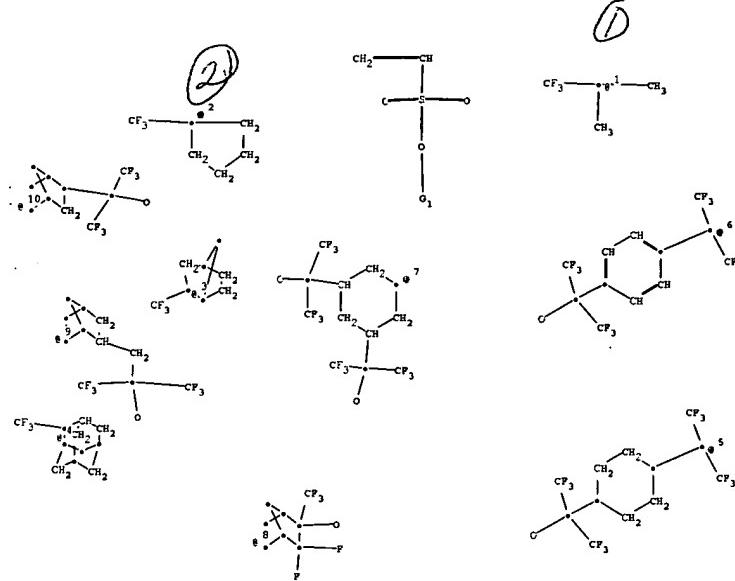
Match level :

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom
10:Atom 11:Atom 12:Atom 13:Atom 15:CLASS 17:CLASS 19:CLASS 20:CLASS
21:Atom 22:Atom 23:CLASS 24:CLASS

Element Count :

Node 15: Limited
C,C1-20

Sulfonate monomers : claim 5



chain nodes :

ring nodes :

chain bonds :

1-2 2-3 3-4 3-5 3-6 4-120 7-10 7-8 7-9 13-39 17-40 25-41 34-43
 37-42 42-44 42-45 43-46 43-47 43-48 50-56 53-55 55-57 55-58 56-59
 56-60 56-61 69-75 71-76 75-77 75-78 75-81 76-79 76-80 76-82 86-92
 86-93 87-90 87-91 97-112 105-108 108-109 108-110 108-111 112-113
 113-114 113-115 113-116

ring bonds :

exact/norm bonds

2-3	3-4	3-5	3-6	4-120	11-12	11-15	12-13	13-14	14-15	16-17	16-21
16-22	17-18	18-19	19-20	19-22	20-21	23-24	23-28	24-25	24-29	25-26	
26-27	26-32	27-28	28-31	29-30	30-31	30-32	33-34	33-38	34-35	35-36	
36-37	37-38	43-48	56-61	69-70	69-74	70-71	71-72	72-73	73-74	75-81	
76-82	83-84	83-88	84-85	85-86	85-89	86-87	87-88	87-91	88-89	94-95	
94-99	95-96	96-97	96-100	97-98	98-99	99-100	101-102	101-106			

102-103

Set bonds :
 1-2 7-10 7-8 7-9 13-39 17-40 25-41 34-43 37-42 42-44 42-45 43-46
 43-47 50-56 53-55 55-57 55-58 56-59 56-60 69-75 71-76 75-77 75-78
 76-79

76-80 86-92 86-93 87-90 97-112 105-108 108-109 108-110
112-113 113-114 113-115
normalized bonds :
49-50 49-54 50-51 51-52 52-53 53-54

G1:[*1],[*2],[*3],[*4],[*5],[*6],[*7],[*8],[*9],[*10]

Match level :

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom
10:Atom 11:Atom 12:Atom 13:Atom 14:Atom 15:Atom 16:Atom 17:Atom
18:Atom 19:Atom 20:Atom 21:Atom 22:Atom 23:Atom 24:Atom 25:Atom
26:Atom 27:Atom 28:Atom 29:Atom 30:Atom 31:Atom 32:Atom 33:Atom
34:Atom 35:Atom 36:Atom 37:Atom 38:Atom 39:Atom 40:Atom 41:Atom
42:Atom 43:Atom 44:Atom 45:Atom 46:Atom 47:Atom 48:Atom 49:Atom
50:Atom 51:Atom 52:Atom 53:Atom 54:Atom 55:Atom 56:Atom 57:Atom
58:CLASS 59:CLASS 60:CLASS 61:CLASS 69:CLASS 70:CLASS 71:CLASS
72:CLASS 73:CLASS 74:CLASS 75:CLASS 76:CLASS 77:CLASS 78:CLASS
79:CLASS 80:CLASS 81:CLASS 82:CLASS 83:CLASS 84:CLASS 85:CLASS
86:CLASS 87:CLASS 88:CLASS 89:CLASS 90:CLASS 91:CLASS 92:CLASS
93:CLASS 94:CLASS 95:CLASS 96:CLASS 97:CLASS 98:CLASS 99:CLASS
100:CLASS 101:Atom 102:Atom 103:Atom 104:Atom 105:Atom 106:Atom
107:Atom 108:CLASS 109:CLASS 110:CLASS 111:CLASS 112:CLASS 113:CLASS
114:CLASS 115:CLASS 116:CLASS 120:CLASS

L3 ANSWER 1 OF 5 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2004:652512 CAPLUS

DN 141:197360

TI Sulfonates, polymers, resist compositions and patterning process

IN Harada, Yuji; Hatakeyama, Jun; Kawai, Yoshio; Sasago, Masaru; Endo, Masayuki; Kishimura, Shinji; Maeda, Kazuhiko; Komoriya, Haruhiko; Miyazawa, Satoru

PA Japan

SO U.S. Pat. Appl. Publ., 26 pp.

CODEN: USXXCO

DT Patent

LA English

FAN CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2004157156	A1	20040812	US 2004-773340	20040209
	JP 2004244436	A2	20040902	JP 2003-32584	20030210

PRAI JP 2003-32584 A 20030210

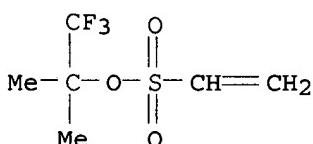
AB A sulfonate compound having formula I ($R1-3 = H, F, C1-20$ alkyl or fluoroalkyl; at least one of $R1-3$ contains F) is novel. A polymer comprising units derived from the sulfonate compound is used as a base resin to formulate a resist composition which is sensitive to high-energy radiation, maintains high transparency at a wavelength of up to 200 nm, and has improved alkali dissoln. contrast and plasma etching resistance.

IT 737765-55-8P 737765-56-9P

RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT (Reactant or reagent)
(preparation of sulfonates, polymers for resist compns. and patterning process)

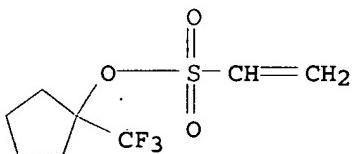
RN 737765-55-8 CAPLUS

CN Ethenesulfonic acid, 2,2,2-trifluoro-1,1-dimethylethyl ester (9CI) (CA INDEX NAME)



RN 737765-56-9 CAPLUS

CN Ethenesulfonic acid, 1-(trifluoromethyl)cyclopentyl ester (9CI) (CA INDEX NAME)



IT 737765-59-2P 737765-60-5P 737765-61-6P

737765-62-7P 737765-63-8P 737765-64-9P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
(sulfonates, polymers for resist compns. and patterning process)

RN 737765-59-2 CAPLUS

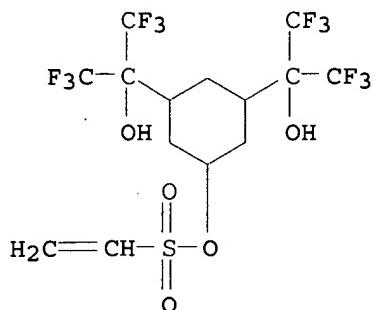
CN Ethenesulfonic acid, 3,5-bis[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl ester, polymer with 2,2,2-trifluoro-1,1-dimethylethyl ethenesulfonate and 5-[3,3,3-trifluoro-2-(methoxymethoxy)-2-

(trifluoromethyl)propyl]bicyclo[2.2.1]hept-2-ene (9CI) (CA INDEX NAME)

CM 1

CRN 737765-58-1

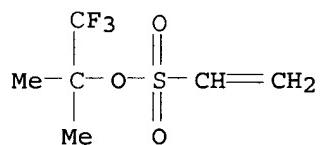
CMF C14 H14 F12 O5 S



CM 2

CRN 737765-55-8

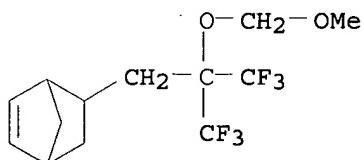
CMF C6 H9 F3 O3 S



CM 3

CRN 450358-92-6

CMF C13 H16 F6 O2



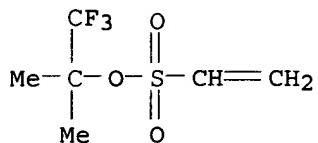
RN 737765-60-5 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol and 2,2,2-trifluoro-1,1-dimethylethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

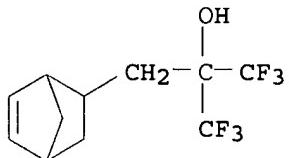
CRN 737765-55-8

CMF C6 H9 F3 O3 S



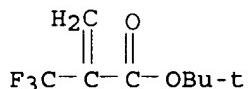
CM 2

CRN 196314-61-1
CMF C11 H12 F6 O



CM 3

CRN 105935-24-8
CMF C8 H11 F3 O2

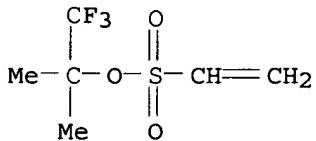


RN 737765-61-6 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with 5-ethenyl- α,α',α' -tetrakis(trifluoromethyl)-1,3-benzenedimethanol and 2,2,2-trifluoro-1,1-dimethylethyl ethenesulfonate (9CI) (CA INDEX NAME)

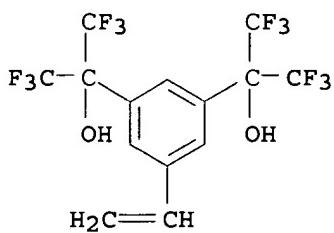
CM 1

CRN 737765-55-8
CMF C6 H9 F3 O3 S



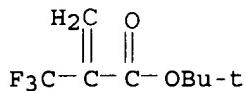
CM 2

CRN 568587-26-8
CMF C14 H8 F12 O2



CM 3

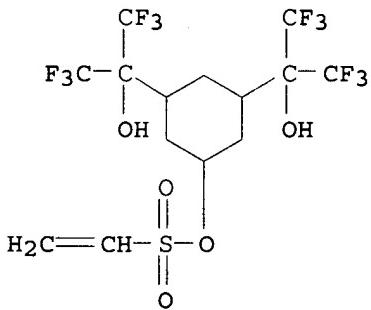
CRN 105935-24-8
CMF C8 H11 F3 O2



RN 737765-62-7 CAPLUS
CN Ethenesulfonic acid, 3,5-bis[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl ester, polymer with 5-[3,3,3-trifluoro-2-(methoxymethoxy)-2-(trifluoromethyl)propyl]bicyclo[2.2.1]hept-2-ene and 1-(trifluoromethyl)cyclopentyl ethenesulfonate (9CI) (CA INDEX NAME)

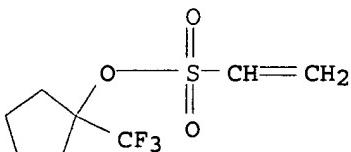
CM 1

CRN 737765-58-1
CMF C14 H14 F12 O5 S



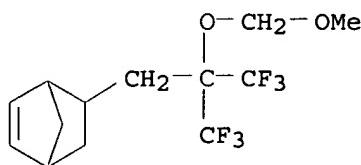
CM 2

CRN 737765-56-9
CMF C8 H11 F3 O3 S



CM 3

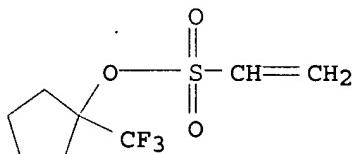
CRN 450358-92-6
CMF C13 H16 F6 O2



RN 737765-63-8 CAPLUS
CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol and 1-(trifluoromethyl)cyclopentyl ethenesulfonate (9CI) (CA INDEX NAME)

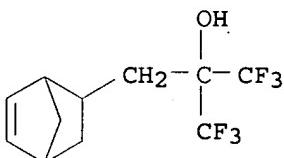
CM 1

CRN 737765-56-9
CMF C8 H11 F3 O3 S



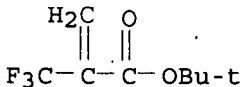
CM 2

CRN 196314-61-1
CMF C11 H12 F6 O



CM 3

CRN 105935-24-8
CMF C8 H11 F3 O2

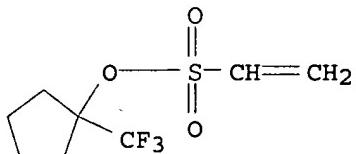


• RN 737765-64-9 CAPLUS
CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with 5-ethenyl- $\alpha,\alpha,\alpha',\alpha'$ -tetrakis(trifluoromethyl)-1,3-benzenedimethanol and 1-(trifluoromethyl)cyclopentyl ethenesulfonate

(9CI) (CA INDEX NAME)

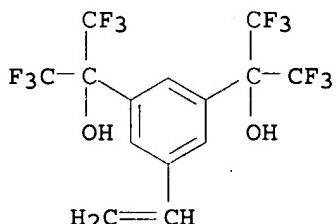
CM 1

CRN 737765-56-9
CMF C8 H11 F3 O3 S



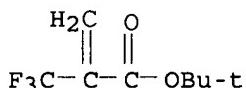
CM 2

CRN 568587-26-8
CMF C14 H8 F12 O2



CM 3

CRN 105935-24-8
CMF C8 H11 F3 O2



L3 ANSWER 2 OF 5 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2004:652511 CAPLUS
DN 141:197359
TI Polymers, resist compositions and patterning process
IN Harada, Yuji; Hatakeyama, Jun; Kawai, Yoshio; Sasago, Masaru; Endo, Masayuki; Kishimura, Shinji; Maeda, Kazuhiko; Komoriya, Haruhiko; Miyazawa, Satoru
PA Japan
SO U.S. Pat. Appl. Publ., 27 pp.
CODEN: USXXCO
DT Patent
LA English
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2004157155	A1	20040812	US 2004-773228	20040209
	JP 2004244439	A2	20040902	JP 2003-32675	20030210
PRAI	JP 2003-32675	A	20030210		

AB A polymer comprising recurring units of I, II (R1 = acid labile group, adhesive group or fluoroalkyl; R2 = H, F, alkyl or fluoroalkyl; R3,4 = single bond, alkylene or fluoroalkylene; R5 = H or an acid labile group; a = 1, 2; 0<U11<1 and 0<U12<1) and having a Mw of 1,000-500,000 is used as a base resin to formulate a resist composition which is sensitive to high-energy radiation, maintains high transparency at a wavelength of up to 200 nm, and has improved alkali dissoln. contrast and plasma etching resistance.

IT 737763-86-9P 737763-88-1P 737763-89-2P

737763-90-5P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
(polymers for resist compns. and patterning process)

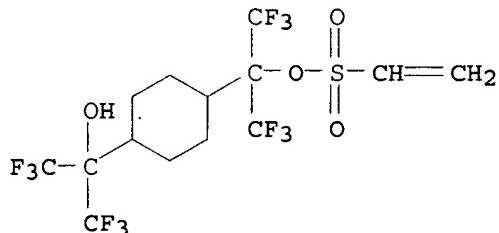
RN 737763-86-9 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 3,5-bis[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl ester, polymer with 5-[3,3,3-trifluoro-2-(methoxymethoxy)-2-(trifluoromethyl)propyl]bicyclo[2.2.1]hept-2-ene and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

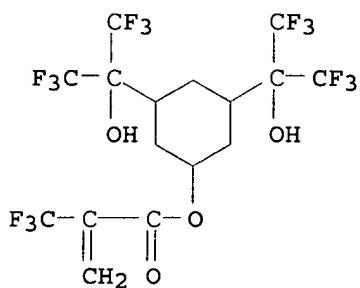
CMF C14 H14 F12 O4 S



CM 2

CRN 585569-92-2

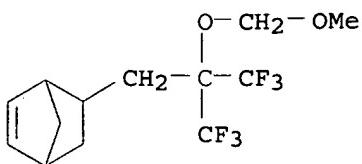
CMF C16 H13 F15 O4



CM 3

CRN 450358-92-6

CMF C13 H16 F6 O2



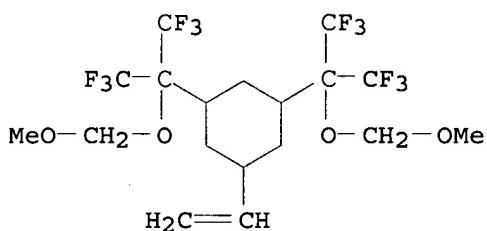
RN 737763-88-1 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 3,5-bis[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl ester, polymer with 1-ethenyl-3,5-bis[2,2,2-trifluoro-1-(methoxymethoxy)-1-(trifluoromethyl)ethyl]cyclohexane and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 737763-87-0

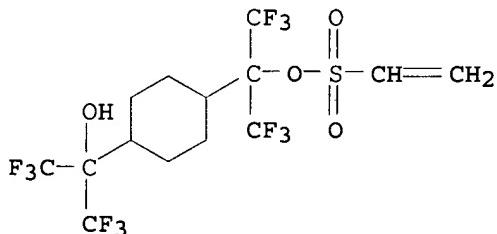
CMF C18 H22 F12 O4



CM 2

CRN 654632-88-9

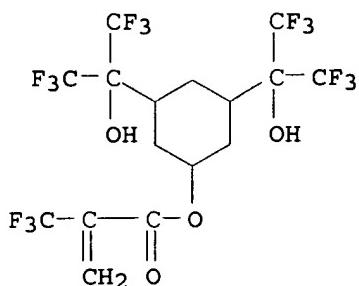
CMF C14 H14 F12 O4 S



CM 3

CRN 585569-92-2

CMF C16 H13 F15 O4



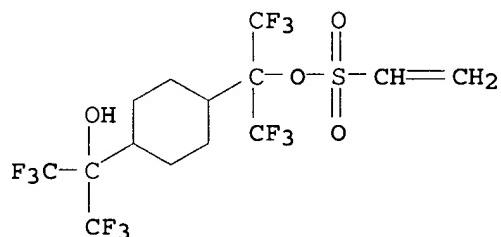
RN 737763-89-2 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 3,5-bis[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl ester, polymer with 1,1-dimethylethyl 2-(trifluoromethyl)-2-propenoate, 5-[3,3,3-trifluoro-2-(methoxymethoxy)-2-(trifluoromethyl)propyl]bicyclo[2.2.1]hept-2-ene and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

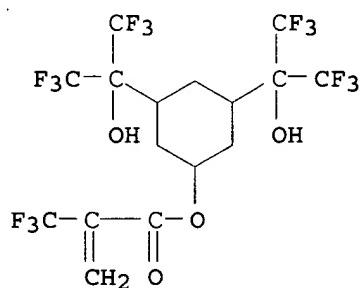
CMF C14 H14 F12 O4 S



CM 2

CRN 585569-92-2

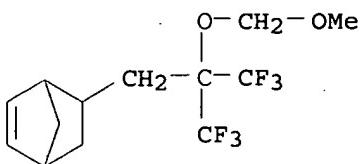
CMF C16 H13 F15 O4



CM 3

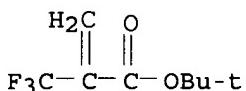
CRN 450358-92-6

CMF C13 H16 F6 O2



CM 4

CRN 105935-24-8
CMF C8 H11 F3 O2

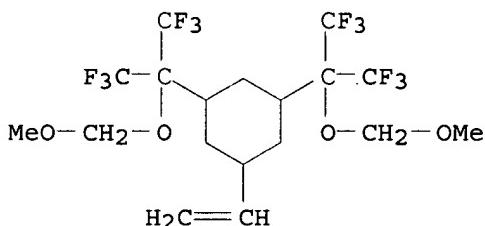


RN 737763-90-5 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 3,5-bis[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl ester, polymer with 1,1-dimethylethyl 2-(trifluoromethyl)-2-propenoate, 1-ethenyl-3,5-bis[2,2,2-trifluoro-1-(methoxymethoxy)-1-(trifluoromethyl)ethyl]cyclohexane and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

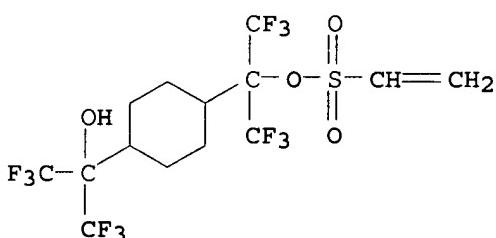
CM 1

CRN 737763-87-0
CMF C18 H22 F12 O4



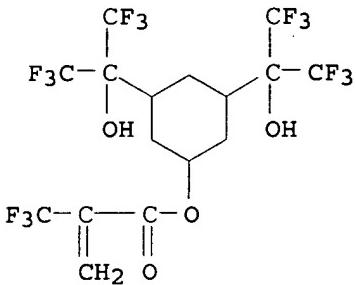
CM 2

CRN 654632-88-9
CMF C14 H14 F12 O4 S



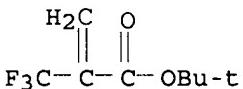
CM 3

CRN 585569-92-2
CMF C16 H13 F15 O4



CM 4

CRN 105935-24-8
CMF C8 H11 F3 O2



L3 ANSWER 3 OF 5 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2004:414469 CAPLUS
DN 140:414952
TI Chemical amplification-type resist material containing sulfonate polymer and patterning method
IN Harada, Yuji; Hatakeyama, Jun; Kawai, Yoshio; Sasako, Masaru; Endo, Masataka; Kishimura, Shinji; Maeda, Kazuhiko; Komoritani, Haruhiko; Miyazawa, Satoru
PA Shin-Etsu Chemical Industry Co., Ltd., Japan; Matsushita Electric Industrial Co., Ltd.; Central Glass Co., Ltd.
SO Jpn. Kokai Tokkyo Koho, 40 pp.
CODEN: JKXXAF
DT Patent
LA Japanese
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2004145048	A2	20040520	JP 2002-310572	20021025
	US 2004144752	A1	20040729	US 2003-690777	20031023
	US 6875556	B2	20050405		

PRAI JP 2002-310572 A 20021025

AB The resist material comprises a polymer compound represented by I ($r_{1,2} = H$, acid unstable group; $0 < a < 1$; $0 < b < 1$; and $0 < (a + b) \leq 1$) and a polymer compound having a sulfonate repeating unit. The resist material further contains a base compound and a dissoln. inhibitor. The process uses a high energy ray with a wavelength 100-180 nm or 1-30 nm to expose the resist material through a photomask. The resist material exhibited high transparency and alkali dissoln. contrast.

IT 654632-89-0 654632-93-6 688785-36-6

688785-38-8 688785-39-9

RL: POF (Polymer in formulation); TEM (Technical or engineered material use); USES (Uses)

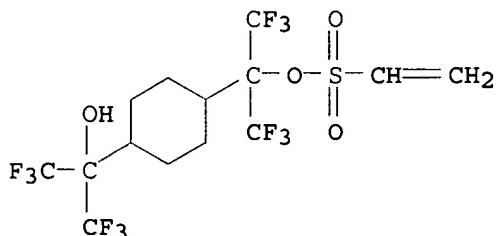
(chemical amplification-type resist material containing sulfonate polymer)

RN 654632-89-0 CAPLUS
CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

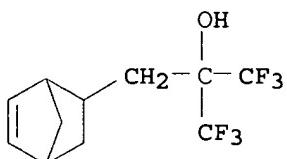
CMF C14 H14 F12 O4 S



CM 2

CRN 196314-61-1

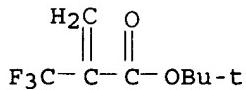
CMF C11 H12 F6 O



CM 3

CRN 105935-24-8

CMF C8 H11 F3 O2



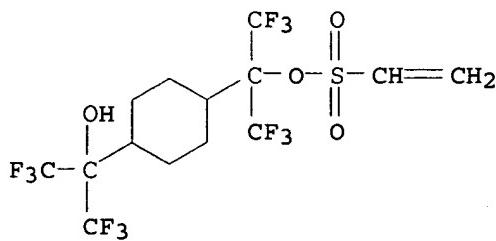
RN 654632-93-6 CAPLUS.

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1;1-dimethylethyl ester, polymer with 5-ethenyl- $\alpha,\alpha,\alpha',\alpha'$ -tetrakis(trifluoromethyl)-1,3-benzenedimethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

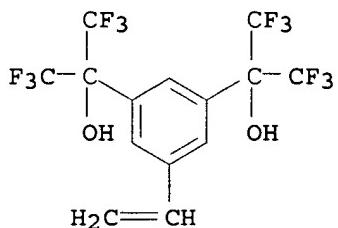
CRN 654632-88-9

CMF C14 H14 F12 O4 S



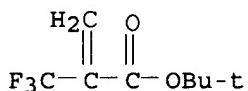
CM 2

CRN 568587-26-8
CMF C14 H8 F12 O2



CM 3

CRN 105935-24-8
CMF C8 H11 F3 O2

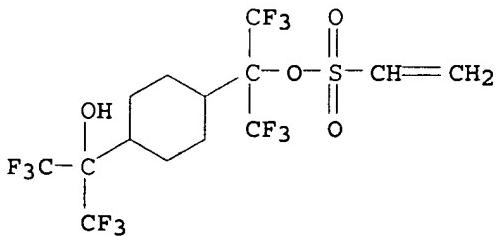


RN 688785-36-6 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with 4-ethenyl- α,α -bis(trifluoromethyl)benzeneethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

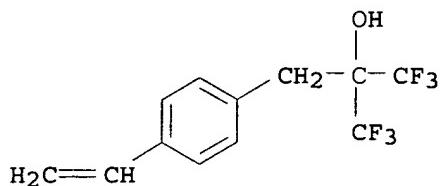
CM 1

CRN 654632-88-9
CMF C14 H14 F12 O4 S



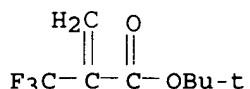
CM 2

CRN 557103-22-7
CMF C12 H10 F6 O



CM 3

CRN 105935-24-8
CMF C8 H11 F3 O2

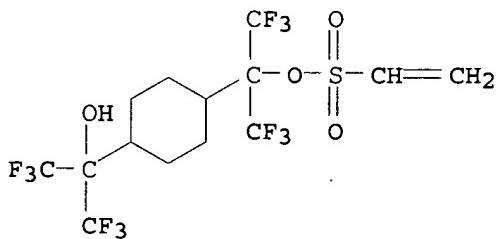


RN 688785-38-8 CAPLUS

CN Ethenesulfonic acid, 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ester, polymer with 1-ethenyl-3,5-bis[2,2,2-trifluoro-1-(methoxymethoxy)-1-(trifluoromethyl)ethyl]benzene and 5-ethenyl- α,α,α' ,.alp ha.'-tetrakis(trifluoromethyl)-1,3-benzenedimethanol (9CI) (CA INDEX NAME)

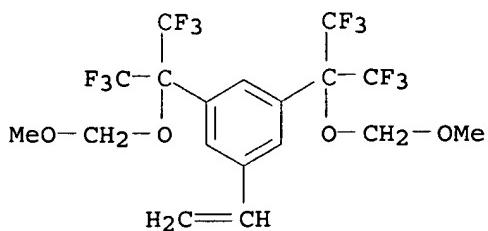
CM 1

CRN 654632-88-9
CMF C14 H14 F12 O4 S



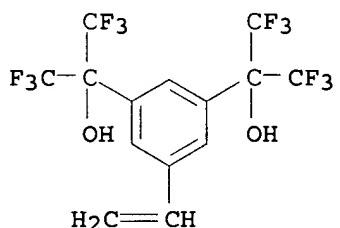
CM 2

CRN 585573-59-7
CMF C18 H16 F12 O4



CM 3

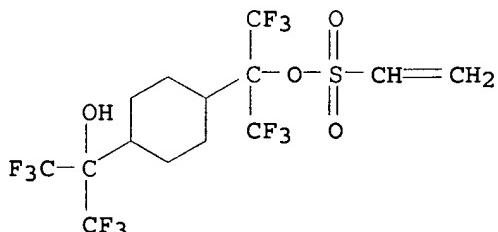
CRN 568587-26-8
CMF C14 H8 F12 O2



RN 688785-39-9 CAPLUS
CN Carbonic acid, (5-ethenyl-1,3-phenylene)bis[2,2,2-trifluoro-1-(trifluoromethyl)ethylidene] bis(1,1-dimethylethyl) ester, polymer with 5-ethenyl- $\alpha,\alpha,\alpha',\alpha'$ -tetrakis(trifluoromethyl)-1,3-benzenedimethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

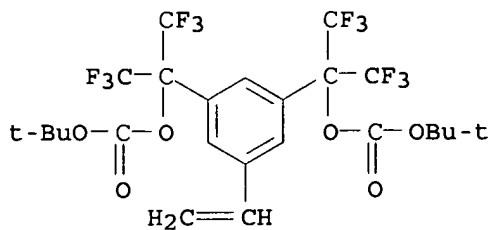
CM 1

CRN 654632-88-9
CMF C14 H14 F12 O4 S



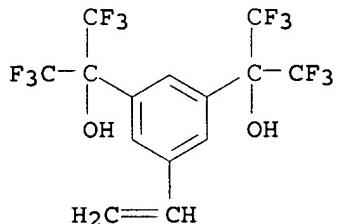
CM 2

CRN 585573-38-2
CMF C24 H24 F12 O6



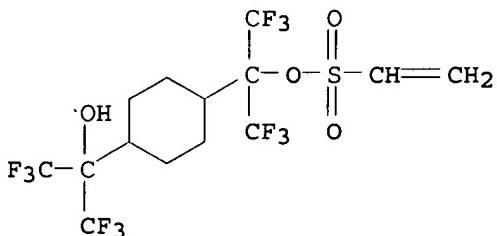
CM 3

CRN 568587-26-8
CMF C14 H8 F12 O2



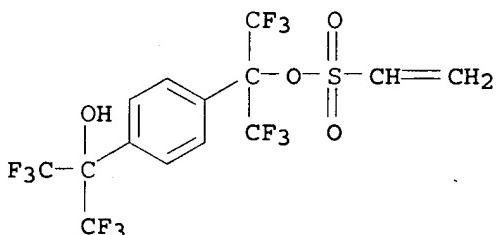
L3 ANSWER 4 OF 5 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2004:200317 CAPLUS
DN 140:218236
TI Manufacture of fluoroalkylcyclohexylfluoroalkyl or
fluoroalkylphenylfluoroalkyl vinylsulfonates
IN Harada, Yuji; Hatakeyama, Jun; Kawai, Yoshio; Maeda, Kazuhiko; Otani,
Michitaka; Komoritani, Haruhiko
PA Shin-Etsu Chemical Industry Co., Ltd., Japan; Central Glass Co., Ltd.
SO Jpn. Kokai Tokkyo Koho, 10 pp.
CODEN: JKXXAF
DT Patent
LA Japanese
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2004075536	A2	20040311	JP 2002-233377	20020809
PRAI	JP 2002-233377		20020809		
OS	MARPAT 140:218236				
AB	The vinylsulfonates, useful as monomers for chemical amplified vacuum-UV resists, are $\text{CH}_2:\text{CHSO}_3\text{CR}_1\text{R}_2\text{XCR}_3\text{R}_4\text{OR}_5$ [I; R1, R2 = H, F, C1-4 alkyl, fluoroalkyl; R1 and/or R2 contain ≥ 1 F; R3 and/or R4 contain ≥ 1 F; R5 = H, acid-labile group, C1-4 oxoalkyl; X = 1,3-cyclohexylene, 1,4-cyclohexylene, 1,3-phenylene, 1,4-phenylene]. Thus, 1,4-di(1,1,1,3,3-hexafluoro-2-hydroxypropyl)cyclohexane was treated with $\text{ClCH}_2\text{CH}_2\text{SO}_2\text{Cl}$ and pyridine to give 53% I (R1-R4 = CF ₃ , R5 = H, X = 1,4-cyclohexylene).				
IT	654632-88-9P 654632-95-8P				
	RL: IMF (Industrial manufacture); PREP (Preparation) (manufacture of fluoroalkylcyclohexylfluoroalkyl or fluoroalkylphenylfluoroalkyl vinylsulfonates as monomers for chemical amplified vacuum-UV resists)				
RN	654632-88-9 CAPLUS				
CN	Ethenesulfonic acid, 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ester (9CI) (CA INDEX NAME)				



RN 654632-95-8 CAPLUS

CN Ethenesulfonic acid, 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]phenyl]-1-(trifluoromethyl)ethyl ester (9CI) (CA INDEX NAME)



L3 ANSWER 5 OF 5 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2004:120612 CAPLUS

DN 140:172201

TI Hydrophilic vinylsulfonate derivative polymers, resist compositions and patterning process

IN Harada, Yuji; Hatakeyama, Jun; Kawai, Yoshio; Sasago, Masaru; Endo, Masayuki; Kishimura, Shinji; Maeda, Kazuhiko; Ootani, Michitaka; Komoriya, Haruhiko

PA Shin-Etsu Chemical Co., Ltd., Japan; Matsushita Electric Industrial Co., Ltd.; Central Glass Co., Ltd.

SO U.S. Pat. Appl. Publ., 30 pp.
CODEN: USXXCO

DT Patent

LA English

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2004030079	A1	20040212	US 2003-636692	20030808
	US 6946235	B2	20050920		
	JP 2004067975	A2	20040304	JP 2002-233194	20020809
	US 2005267275	A1	20051201	US 2005-179606	20050713
PRAI	JP 2002-233194	A	20020809		
	US 2003-636692	A3	20030808		

AB A resist composition comprising a polymer containing vinyl sulfonate units having

fluorinated hydrophilic groups based on fluorinated cyclohexane or Ph ring having ether- or OH-containing groups as a base resin has excellent transparency, substrate adhesion and developer penetrability as well as plasma etching resistance, and is suited for lithog. microprocessing. A typical resin was manufactured by radical polymerization of 7 g

2-[4-(2-hydroxy-

1,1,1,3,3,3-hexafluoro-2-propyl)cyclohexyl]-1,1,1,3,3,3-hexafluoro-2-Pr vinylsulfonate with 7.58 g 6-[2-hydroxy-2-(trifluoromethyl)-3,3,3-trifluoropropyl]norbornene and 5.42 g CH₂=C(CF₃)CO₂CMe₃.

IT **654632-89-0P** **654632-90-3P** **654632-91-4P**
654632-92-5P **654632-93-6P** **654632-94-7P**

654632-96-9P

PL: IMF (Ind)

RL: IMF (Industrial manufacture); IEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(polymers containing vinyl sulfonate units having fluorinated hydrophilic groups based on fluorinated cyclohexane or Ph ring having ether- or OH-containing groups for photoresists)

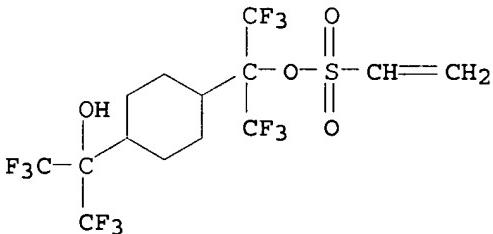
RN 654632-89-0 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

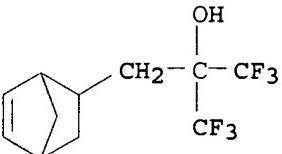
CMF C14 H14 F12 O4 S



CM 2

CRN 196314-61-1

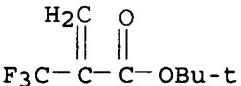
CMF C11 H12 F6 O



CM 3

CRN 105935-24-8

CMF C8 H11 F3 O2



RN 654632-90-3 CAPLUS

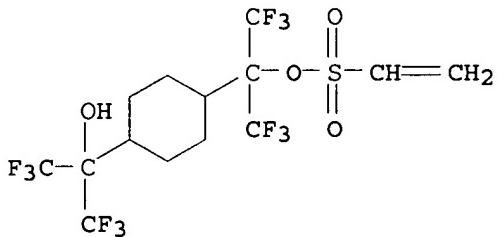
CN 2-Propenoic acid, 2-(trifluoromethyl)-, 2-methyltricyclo[3.3.1.13,7]dec-2-yl ester, polymer with α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl

ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

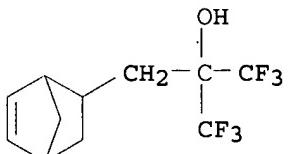
CMF C14 H14 F12 O4 S



CM 2

CRN 196314-61-1

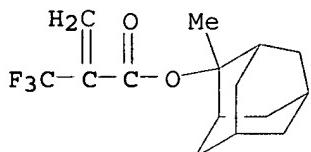
CMF C11 H12 F6 O



CM 3

CRN 188739-86-8

CMF C15 H19 F3 O2



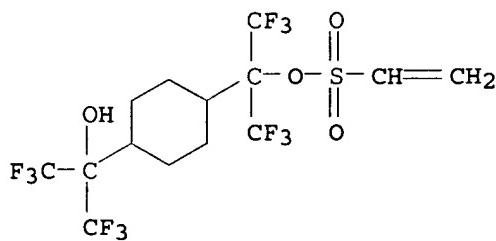
RN 654632-91-4 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with 4-ethenyl-alpha,alpha-bis(trifluoromethyl)benzenemethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

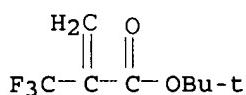
CRN 654632-88-9

CMF C14 H14 F12 O4 S



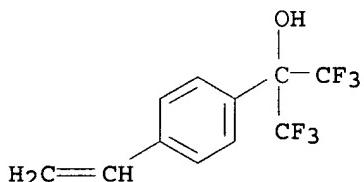
CM 2

CRN 105935-24-8
CMF C8 H11 F3 O2



CM 3

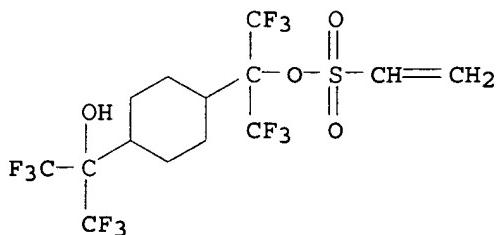
CRN 2386-82-5
CMF C11 H8 F6 O



RN 654632-92-5 CAPLUS
CN 2-Propenoic acid, 2-(trifluoromethyl)-, 2-methyltricyclo[3.3.1.13,7]dec-2-yl ester, polymer with 4-ethenyl- α,α -bis(trifluoromethyl)benzenemethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

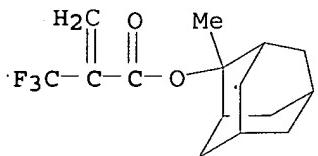
CM 1

CRN 654632-88-9
CMF C14 H14 F12 O4 S



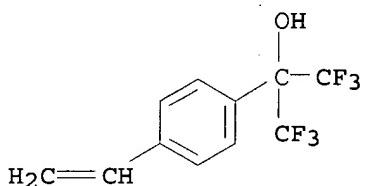
CM 2

CRN 188739-86-8
CMF C15 H19 F3 O2



CM 3

CRN 2386-82-5
CMF C11 H8 F6 O

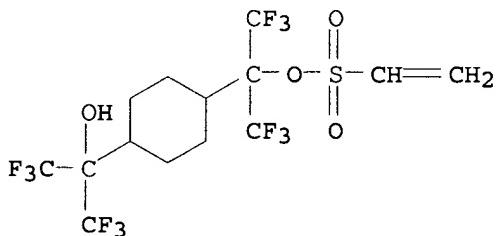


RN 654632-93-6 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with 5-ethenyl- α,α',α' -tetrakis(trifluoromethyl)-1,3-benzenedimethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

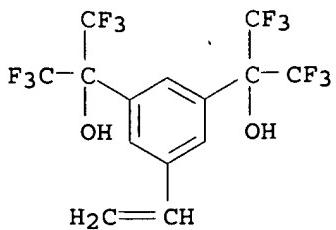
CM 1

CRN 654632-88-9
CMF C14 H14 F12 O4 S



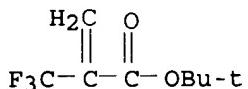
CM 2

CRN 568587-26-8
CMF C14 H8 F12 O2



CM 3

CRN 105935-24-8
CMF C8 H11 F3 O2

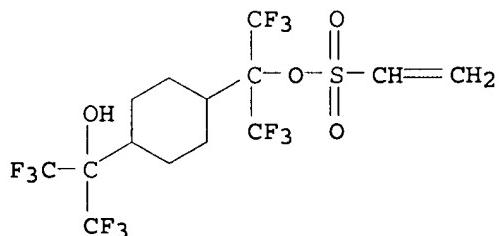


RN 654632-94-7 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 2-methyltricyclo[3.3.1.13,7]dec-2-yl ester, polymer with 5-ethenyl- $\alpha,\alpha,\alpha',\alpha'$ -tetrakis(trifluoromethyl)-1,3-benzenedimethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

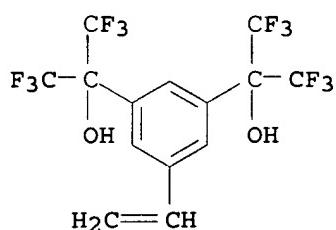
CM 1

CRN 654632-88-9
CMF C14 H14 F12 O4 S



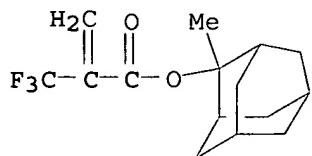
CM 2

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CMF C14 H8 F12 O2



CM 3

CRN 188739-86-8
CMF C15 H19 F3 O2

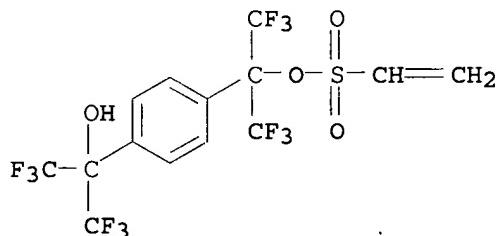


RN 654632-96-9 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with 5-ethenyl- $\alpha,\alpha,\alpha',\alpha'$ -tetrakis(trifluoromethyl)-1,3-benzenedimethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]phenyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

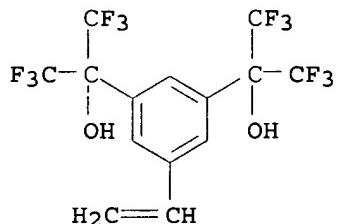
CM 1

CRN 654632-95-8
CMF C14 H8 F12 O4 S



CM 2

CRN 568587-26-8
CMF C14 H8 F12 O2



CM 3

CRN 105935-24-8
CMF C8 H11 F3 O2